

PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

INJ0E22AG1

High Speed Switching
Silicon P-channel MOSFET

DESCRIPTION

INJ0E22AG1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery,
because of low voltage drive and low on resistance.

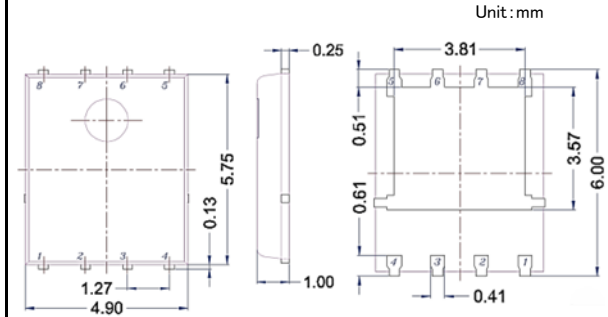
FEATURE

- Low on-resistance $R_{DS(ON)}$: max. $12\text{m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=-17\text{A}$.
- High drain current $I_D=-17\text{A}$
- Drive voltage -4.0V
- High speed switching.

APPLICATION

Switching Regulator, DC/DC Converter

OUTLINE DRAWING



TERNIMAL CONNECTOR

JEITA: HSOP8

- ① : SOURCE
- ② : SOURCE
- ③ : SOURCE
- ④ : GATE
- ⑤ : DRAIN
- ⑥ : DRAIN
- ⑦ : DRAIN
- ⑧ : DRAIN

MAXIMUM RATINGS

Paramete	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Drain Current(DC)(※1) $T_a=25^\circ\text{C}$	I_D	-17	A
Drain Current(Pulse) (※2)	I_{DP}	-28	A
Total Power Dissipation (※1)	P_D	3	W
Channel Temperature	T_{ch}	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

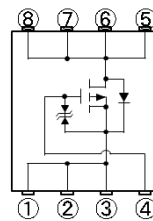
※1 package mounted on glass-epoxy substrate.

39mm × 39mm × 1.6mm

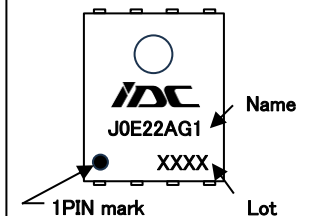
Copper foil with an area of 1460 mm² and a thickness of 35 μm

※2 : $P_w \leq 10\text{ms}$, Duty cycle $\leq 1\%$

EQUIVALENT CIRCUIT



MARKING



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30	-	-	V
Gate-Source Leak Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	-	-	± 0.1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$	-	-	-100	μA
Gate Threshold Voltage	V_{th}	$I_D=-250\mu\text{A}$, $V_{DS}=V_{GS}$	-1.0	-	-2.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D=-17\text{A}$, $V_{GS}=-10\text{V}$	-	9.5	12	$\text{m}\Omega$
		$I_D=-12\text{A}$, $V_{GS}=-4.5\text{V}$	-	13	17	
Input Capacitance	C_{iss}	$V_{DS}=-10\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	-	3780	-	pF
Output Capacitance	C_{oss}		-	530	-	
Feedback Capacitance	C_{rss}		-	330	-	
Switching Time	t_{on}	$V_{DS}=-20\text{V}$, $I_D=-200\text{mA}$, $f=1\text{MHz}$	-	350	-	ns
	t_{off}		-	920	-	

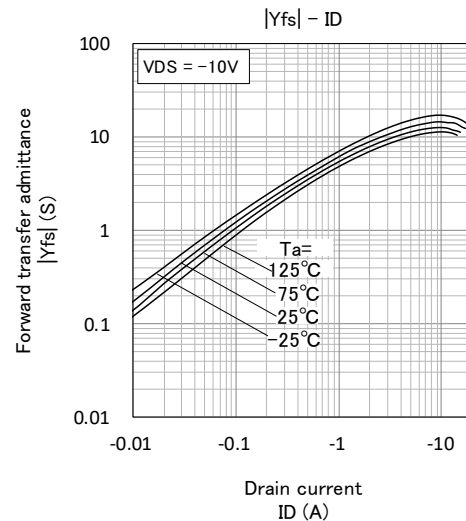
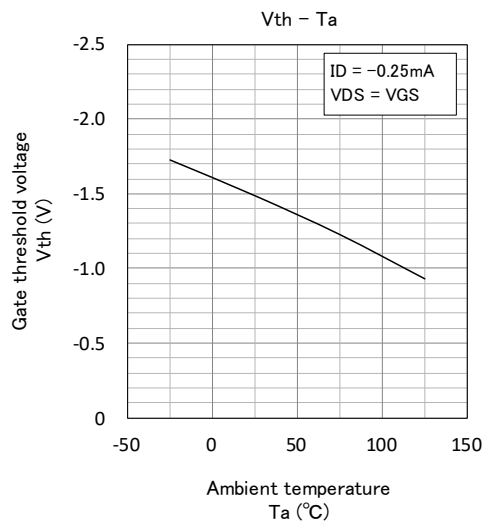
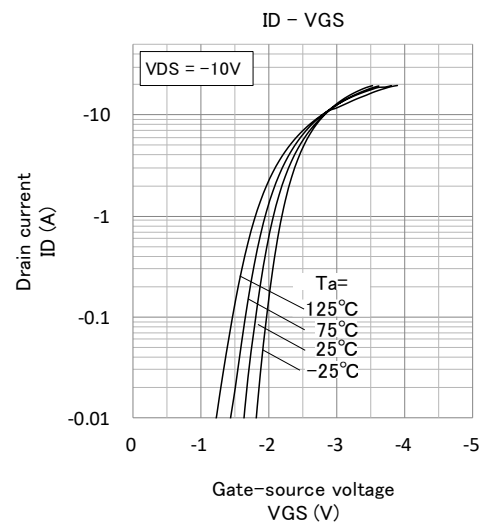
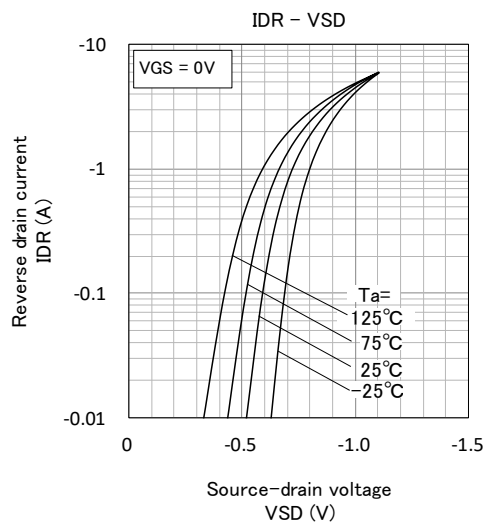
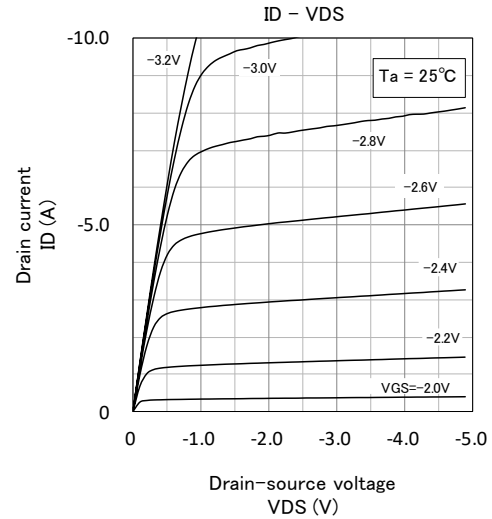
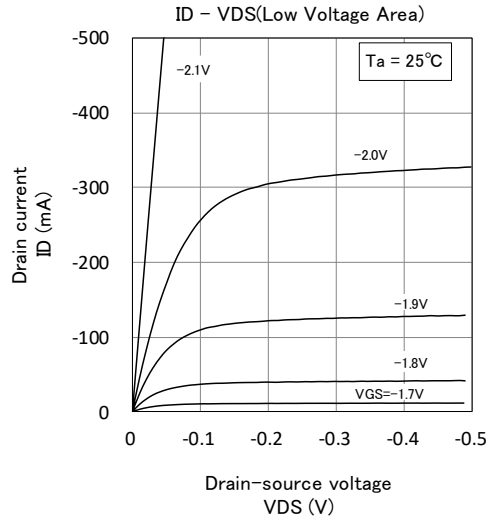
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TYPICAL CHARACTERISTICS

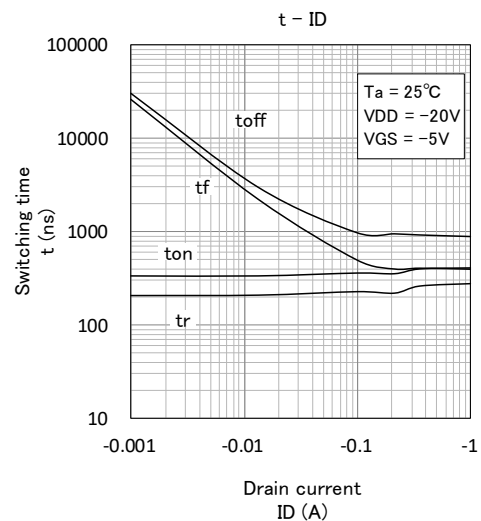
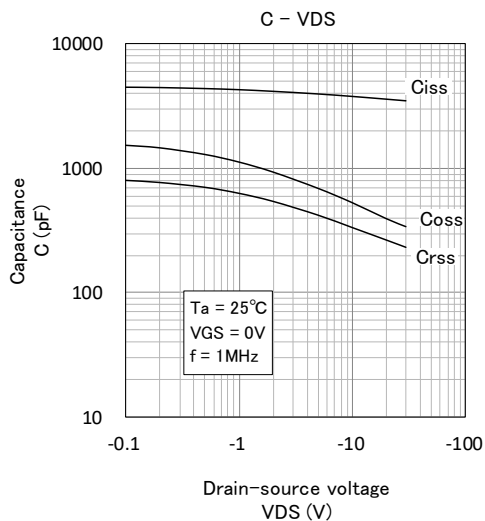
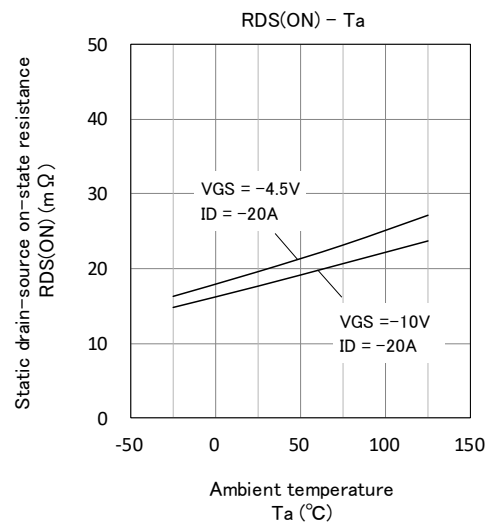
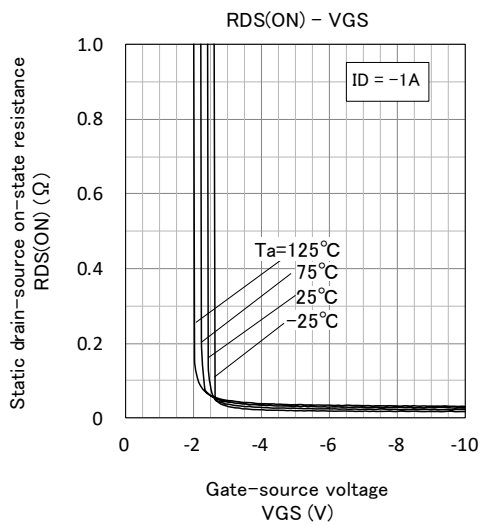
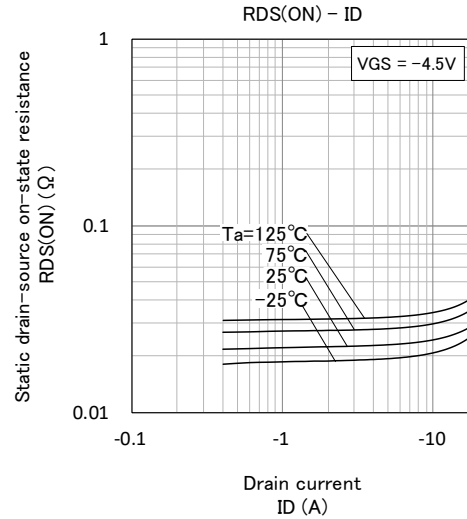
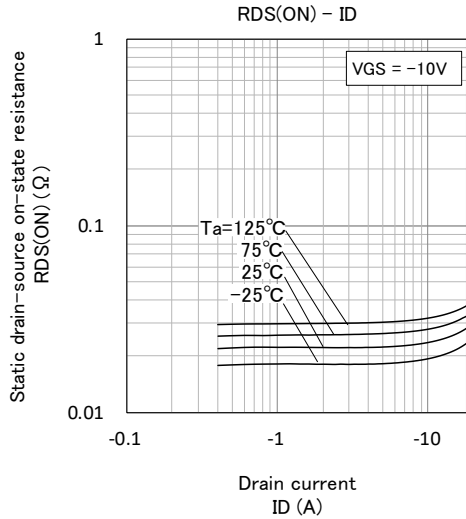


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